

**1. Scope :**

This specification applies to P/N silicon zener diode chips,  
Device NO. SD-30860G

**2. Structure :**

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :  
Top side : Gold pad.  
Back side : Gold layer.

**3. Size :**

- 3-1. <sup>※1</sup>Chip size : 8.5 mils x 8.5 mils (0.215 mm x 0.215 mm ).
- 3-2. Chip thickness : 4.0 ± 1.0 mils (0.100 ± 0.0254 mm ).
- 3-3. Active area : 5.3 mils x 5.3 mils (0.135 mm x 0.135 mm).
- 3-4. <sup>※2</sup>Bonding pad : 5.9 mils x 5.9 mils (0.150 mm x 0.150 mm) .
- 3-5. Pattern drawing : Refer to the attached drawing.  
<sup>※1</sup>Including scribing line. The chip size is about (0.190±0.015)<sup>2</sup>mm<sup>2</sup> after dicing.  
<sup>※2</sup>The bonding pad dimension is (0.150±0.005)<sup>2</sup>mm<sup>2</sup>.

**4. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> =4V Ee=0mW/cm <sup>2</sup>			100	nA
		V <sub>R</sub> =5V Ee=0mW/cm <sup>2</sup>			0.5	μ A
Zener Voltage	V <sub>Z</sub>	I <sub>Z</sub> =5mA Ee=0mW/cm <sup>2</sup>	5.8		6.8	V
Forward Voltage	V <sub>f</sub>	I <sub>F</sub> =20mA Ee=0mW/cm <sup>2</sup>			1.2	V

